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RoHS

COMPLIANT HALOGEN

FREE

GREEN (5-2008)



Vishay Semiconductors

High Speed Infrared Emitting Diode, 940 nm, GaAlAs, MQW



DESCRIPTION

VSMB11940X01 is an infrared, 940 nm side looking emitting diode in GaAlAs multi quantum well (MQW) technology with high radiant power and high speed, molded in clear, untinted plastic package (with lens) for surface mounting (SMD).

FEATURES

- Package type: surface-mount
- · Package form: side view
- Dimensions (L x W x H in mm): 3 x 2 x 0.6
- AEC-Q101 qualified
- Peak wavelength: λ_p = 940 nm
- · High reliability
- High radiant power
- · High radiant intensity
- · High speed
- Angle of half intensity: $\varphi = \pm 75^{\circ}$
- Low forward voltage
- Package matches with detector VEMD11940FX01
- Floor life: 168 h, MSL 3, according to J-STD-020
- · Lead (Pb)-free reflow soldering
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

APPLICATIONS

- IR touch panel
- · High power emitter for low space applications
- High performance transmissive or reflective sensors

PRODUCT SUMMARY				
COMPONENT	I _e (mW/sr), 20 mA	φ (°)	$\lambda_{\mathbf{p}}$ (nm)	t _r (ns)
VSMB11940X01	1	± 75	940	15

Note

· Test conditions see table "Basic Characteristics"

ORDERING INFORMATION					
ORDERING CODE	PACKAGING	REMARKS	PACKAGE FORM		
VSMB11940X01	Tape and reel	MOQ: 4000 pcs, 4000 pcs/reel	side view		

Note

• MOQ: minimum order quantity

ABSOLUTE MAXIMUM RATINGS (T _{amb} = 25 °C, unless otherwise specified)					
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT	
Reverse voltage		V _R	5	V	
Forward current		I _F	65	mA	
Peak forward current	$t_p/T = 0.5, t_p = 100 \mu s$	I _{FM}	130	mA	
Surge forward current	t _p = 100 μs	I _{FSM}	500	mA	
Power dissipation		P _V	104	mW	
Junction temperature		Tj	100	°C	
Operating temperature range		T _{amb}	-40 to +85	°C	
Storage temperature range		T _{stg}	-40 to +100	°C	
Soldering temperature	According to Fig. 9, J-STD-020	T _{sd}	260	°C	
Thermal resistance junction / ambient	JESD 51	R _{thJA}	580	K/W	

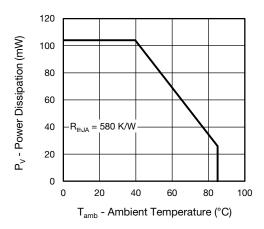
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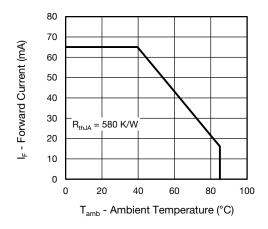


Fig. 2 - Forward Current Limit vs. Ambient Temperature

BASIC CHARACTERISTICS (T _{amb} = 25 °C, unless otherwise specified)						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Forward voltage	$I_F = 20 \text{ mA}, t_p = 20 \text{ ms}$	V_{F}	1.1	1.24	1.5	V
	$I_F = 65 \text{ mA}, t_p = 20 \text{ ms}$	V _F	-	1.35	-	V
	$I_F = 500 \text{ mA}, t_p = 100 \mu \text{s}$	V _F	-	1.8	-	V
Temperature coefficient of V _F	I _F = 1 mA	TK _{VF}	-	-1.5	-	mV/K
Reverse current	V _R = 5 V	I _R	-	-	10	μΑ
Junction capacitance	$V_R = 0 \text{ V, f} = 1 \text{ MHz,}$ $E = 0 \text{ mW/cm}^2$	CJ	-	21	-	pF
	$I_F = 20 \text{ mA}, t_p = 20 \text{ ms}$	l _e	0.5	1.0	1.5	mW/sr
Radiant intensity	$I_F = 65 \text{ mA}, t_p = 20 \text{ ms}$	l _e	-	3.2	-	mW/sr
	$I_F = 500 \text{ mA}, t_p = 100 \mu \text{s}$	l _e	-	20	-	mW/sr
Radiant power	$I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$	фе	-	35	-	mW
Temperature coefficient of radiant power	I _F = 100 mA	TKφ _e	-	-0.47	-	%/K
Angle of half intensity - horizontal		φ _h	-	± 77.5	-	0
Angle of half intensity - vertical		φν	-	± 72.5	-	0
Peak wavelength	I _F = 30 mA	λ_{p}	-	940	-	nm
Spectral bandwidth	I _F = 30 mA	Δλ	-	25	-	nm
Temperature coefficient of λ_p	I _F = 30 mA	TK_{\lambdap}	-	0.3	-	nm
Rise time	I _F = 100 mA, 20 % to 80 %	t _r	-	15	-	ns
Fall time	I _F = 100 mA, 20 % to 80 %	t _f	-	15	-	ns

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BASIC CHARACTERISTICS (T_{amb} = 25 °C, unless otherwise specified)

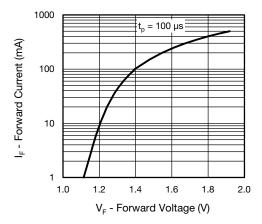


Fig. 3 - Forward Current vs. Forward Voltage

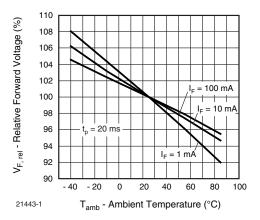


Fig. 4 - Relative Forward Voltage vs. Ambient Temperature

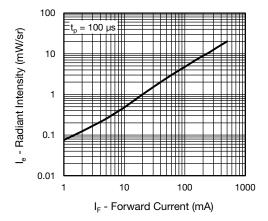


Fig. 5 - Radiant Intensity vs. Forward Current

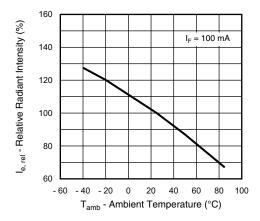


Fig. 6 - Relative Radiant Intensity vs. Ambient Temperature

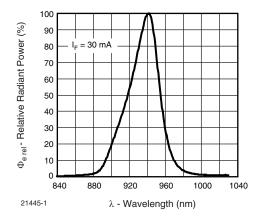


Fig. 7 - Relative Radiant Power vs. Wavelength

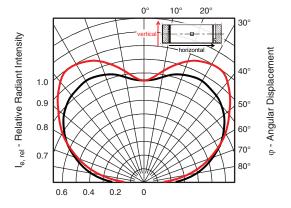


Fig. 8 - Relative Radiant Intensity vs. Angular Displacement



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REFLOW SOLDER PROFILE

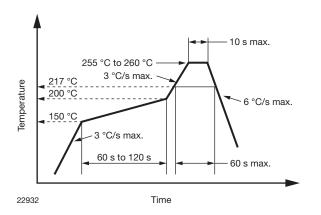


Fig. 9 - Lead (Pb)-free Reflow Solder Profile According to J-STD-020

DRYPACK

Devices are packed in moisture barrier bags (MBB) to prevent the products from moisture absorption during transportation and storage. Each bag contains a desiccant.

FLOOR LIFE

Time between soldering and removing from MBB must not exceed the time indicated in J-STD-020:

Moisture sensitivity: level 3

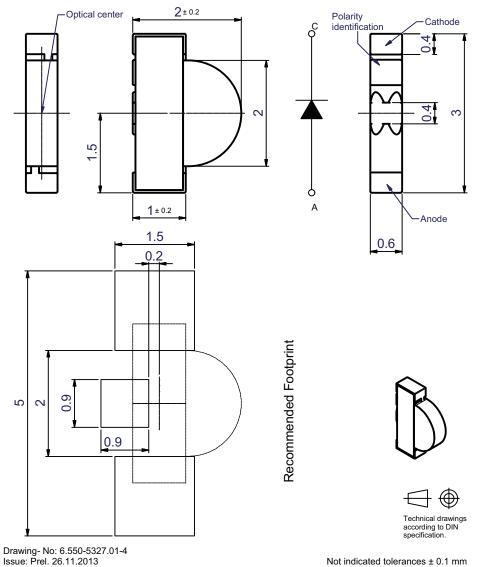
Floor life: 168 h

Conditions: T_{amb} < 30 °C, RH < 60 %

DRYING

In case of moisture absorption devices should be baked before soldering. Conditions see J-STD-020 or label. Devices taped on reel dry using recommended conditions 192 h at 40 $^{\circ}$ C (+ 5 $^{\circ}$ C), RH < 5 $^{\circ}$ M.

PACKAGE DIMENSIONS in millimeters

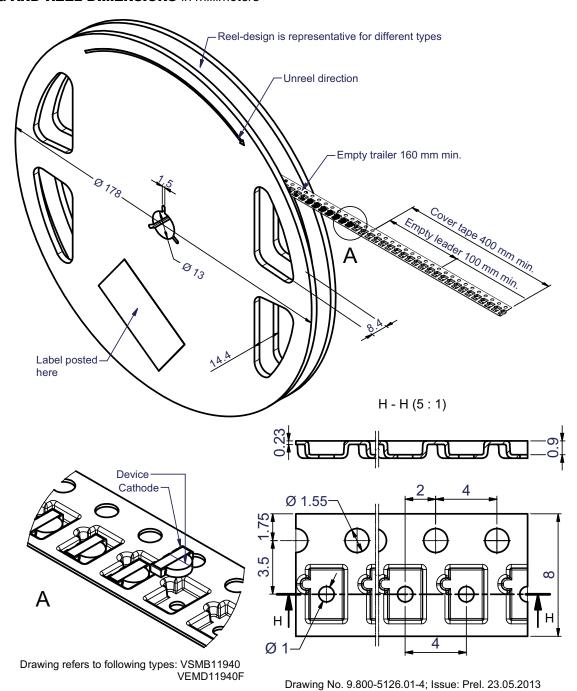


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TAPING AND REEL DIMENSIONS in millimeters



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